

<b>Notice of References Cited</b>	Application/Control No. <b>09/766,046</b>	Applicant(s)/Patent Under Reexam <b>Ramdani et al.</b>	
	Examiner <b>B. William Baumeister</b>	Art Unit <b>2815</b>	Page 1 of 2

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**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Kaushik, "Device Characteristics of Crystalline Epitaxial Oxides on Silicon," 58th Annual Device Research Conference June 19-21, 2000, pp. 17-20.
V	Eisenbeiser et al., Field effect transistors with SrTiOs gate dielectric on Si," 6 March 2000, Applied Physics Letters, Vol. 76, No. 10, pp. 1324-1326.
W	Weiss, "Speed demon gets hooked on silicon," Science News Online, 9/15/2001.
X	"Motorola develops new super-fast chip," USA Today, 9/4/2001.

\* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a). <sup>1</sup> Dates in MM-YYYY format are publication dates. <sup>2</sup> Classifications may be U.S. or foreign.

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	U	Valigra, "Motorola Lays GaAs on Si Wafer," AsiaBiz Tech, Nov: 2001.
	V	"Holy Grail! Motorola claims high-yield GaAs breakthrough," Micromagazine.com (no date available).
	W	
	X	

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